

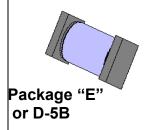
1N5807US thru 1N5811US

SURFACE MOUNT VOIDLESS-HERMETICALLY-SEALED ULTRA FAST RECOVERY GLASS RECTIFIERS

DESCRIPTION

This "Ultrafast Recovery" surface mount rectifier diode series is military qualified to MIL-PRF-19500/477 and is ideal for high-reliability applications where a failure cannot be tolerated. These industry-recognized 6.0 Amp rated rectifiers for working peak reverse voltages from 50 to 150 volts are hermetically sealed with voidless-glass construction using an internal "Category I" metallurgical bond. These devices are also available in axial-leaded package configurations (see separate data sheet for 1N5807 thru 1N5811). Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time speed requirements including standard, fast, and ultrafast device types in both throughhole and surface mount packages.

APPEARANCE



IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

FEATURES

- Surface mount package series equivalent to the JEDEC registered 1N5807 to 1N5811 series
- · Voidless-hermetically-sealed glass package
- · Extremely robust construction
- Triple-layer passivation
- Internal "Category I" Metallurgical bonds
- JAN, JANTX, JANTXV, and JANS available per MIL-PRF-19500/477
- Axial-leaded equivalents also available (see separate data sheet for 1N5807 thru 1N5811)

MAXIMUM RATINGS

- Operating Temperature: -65°C to +175°C.
- Storage Temperature: -65°C to +175°C.
- Average Rectified Forward Current (I_O): 6 Amps @ T_{EC} = 75°C End Cap temperature (see note 1)
- Thermal Resistance: 10 °C/W junction to end cap
- Thermal Impedance: 1.5 °C/W @ 10 ms heating time
- Forward Surge Current (8.3 ms half sine) 125 Amps
- Solder temperature: 260°C for 10 s (maximum)

APPLICATIONS / BENEFITS

- Ultrafast recovery 6 Amp rectifiers series 50 to 150 V
- Military and other high-reliability applications
- Switching power supplies or other applications requiring extremely fast switching & low forward loss
- High forward surge current capability
- Low thermal resistance
- Controlled avalanche with peak reverse power capability
- Inherently radiation hard as described in Microsemi MicroNote 050

MECHANICAL AND PACKAGING

- CASE: Hermetically sealed voidless hard glass with Tungsten slugs
- TERMINALS: End caps are solid Silver with Tin/Lead (Sn/Pb) finish
- MARKING & POLARITY: Cathode band only
- Tape & Reel option: Standard per EIA-481-B
 - Weight: 539 mg
- See package dimensions and recommended pad layout on last page

ELECTRICAL CHARACTERISTICS

TYPE	WORKING PEAK REVERSE VOLTAGE V _{RWM}	BREAKDOWN VOLTAGE (MIN.) @ 100µA V _{BR}	AVERAGE RECTIFIED CURRENT I _{O1} @T _{EC} =75°C (Note 1)	AVERAGE RECTIFIED CURRENT I _{O2} @T _A =55°C (Note 2)	FORV VOLT @ 4 (8.3 ms	IMUM VARD FAGE 4 A s pulse) / _F	CUR (M @ V	ERSE RENT AX) RWM	SURGE CURRENT (MAX) I _{FSM} (NOTE 3)	REVERSE RECOVERY TIME (MAX) (NOTE 4) t _{rr}
	VOLTS	VOLTS	AMPS	AMPS	VOL	_TS		ιA	AMPS	ns
					25°C	100°C	25°C	100°C		
1N5807US	50	60	6.0	3.0	0.875	0.800	5	150	125	30
1N5809US	100	110	6.0	3.0	0.875	0.800	5	150	125	30
1N5811US	150	160	6.0	3.0	0.875	0.800	5	150	125	30

NOTE 1: Rated at T_{EC} = 75°C. Derate at 60 mA/°C for T_{EC} above 75°C

NOTE 2: Derate linearly at 25 mA/°C above T_A = 55°C. This rating is typical for PC boards where thermal resistance from mounting point to ambient is sufficiently controlled where T_{J(max)} does not exceed 175°C

NOTE 3: $T_A = 25^{\circ}C @ I_O = 3.0 A$ and V_{RWM} for ten 8.3 ms surges at 1 minute intervals

NOTE 4: $I_F = 1.0 \text{ A}$, $I_{RM} = 1.0 \text{ A}$, $I_{R(REC)} = 0.10 \text{ A}$ and $di/dt = 100 \text{ A}/\mu \text{s min}$





1N5807US thru 1N5811US

SURFACE MOUNT VOIDLESS-HERMETICALLY-SEALED ULTRA FAST RECOVERY GLASS RECTIFIERS

SYMBOLS & DEFINITIONS					
Symbol	Definition				
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.				
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.				
V _F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.				
I _R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature.				
С	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage				
t _{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified recovery decay point after a peak reverse current is reached.				

GRAPHS

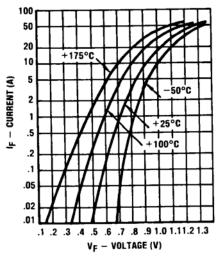
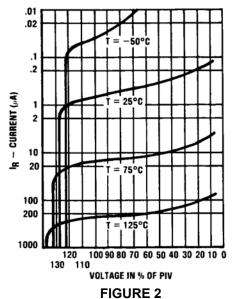
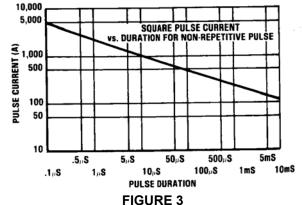


FIGURE 1
TYPICAL FORWARD CURRENT
vs. FORWARD VOLTAGE



TYPICAL REVERSE CURRENT vs. VOLTAGE

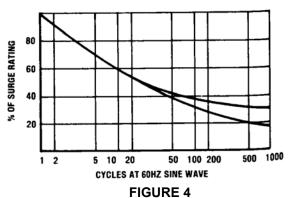


FORWARD PULSE CURRENT vs. DURATION



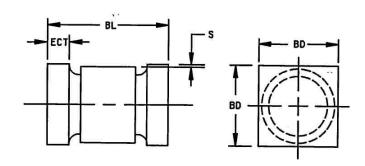
1N5807US thru 1N5811US

SURFACE MOUNT VOIDLESS-HERMETICALLY-SEALED ULTRA FAST RECOVERY GLASS RECTIFIERS



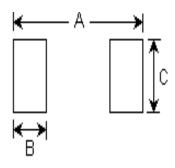
MULTIPLE SURGE CURRENT vs. DURATION

PACKAGE DIMENSIONS AND PAD LAYOUT



NOTE: This Package Outline has also previously been identified as "D-5B"

	INC	HES	mm		
	MIN	MAX	MIN	MAX	
BL	.205	.225	5.21	5.72	
BD	.137	.142	3.48	3.61	
ECT	.019	.028	0.48	0.711	
S	.003		0.08		



PAD LAYOUT

	INCHES	mm
Α	0.288	7.32
В	0.070	1.78
С	0.155	3.94

Note: If mounting requires adhesive separate from the solder, an additional 0.080 inch diameter contact may be placed in the center between the pads as an optional spot for cement